

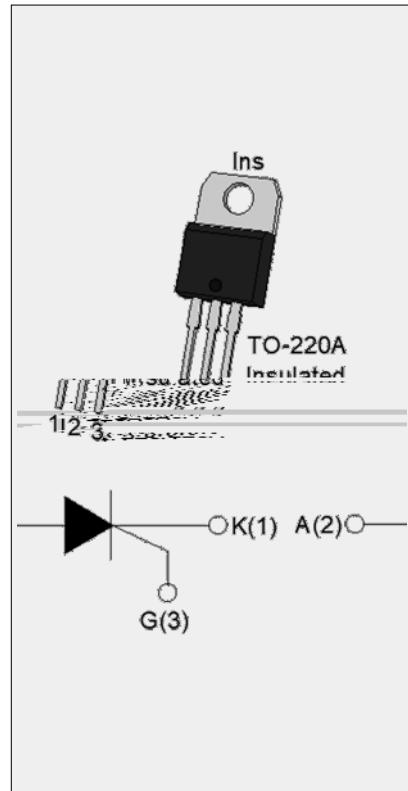


## DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1625A SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT1625A provides a rated insulation voltage of 2500 V<sub>RMS</sub>, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.

## MAIN FEATURES

Symbol	Value	Unit
I <sub>T(RMS)</sub>	25	A
V <sub>DRM/V<sub>RRM</sub></sub>	1600	V
I <sub>GT</sub>	40	mA



## ABSOLUTE MAXIMUM RATINGS

Storage junction temperature range	T <sub>stg</sub>	-40-150	
Operating junction temperature range	T <sub>j</sub>	-40-125	
Repetitive peak off-state voltage (T <sub>j</sub> =25 °C)	V <sub>DRM</sub>	1600	V
Repetitive peak reverse voltage (T <sub>j</sub> =25 °C)	V <sub>RRM</sub>	1600	V
Average on-state current (T <sub>c</sub> = 48 °C)	I <sub>T(AV)</sub>	16	A
RMS on-state current (T <sub>c</sub> = 48 °C)	I <sub>T(RMS)</sub>	25	A
Non repetitive surge peak on-state current (t <sub>p</sub> =10ms, T <sub>j</sub> =25 °C)	I <sub>TSM</sub>	280	A
Non repetitive surge peak on-state current (t <sub>p</sub> =8.3ms, T <sub>j</sub> =25 °C)		300	
I <sup>2</sup> t value for fusing (t <sub>p</sub> =10ms, T <sub>j</sub> =25 °C)	I <sup>2</sup> t	392	A <sup>2</sup> s
Critical rate of rise of on-state current (I <sub>G</sub> =2× I <sub>GT</sub> , f=100Hz, T <sub>j</sub> =125 °C)	dI/dt	200	A/μs



Peak gate current ( $t_p=20\mu s$ , $T_j=125$ )	$I_{GM}$	5	A
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	20	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	1.5	kV

### ELECTRICAL CHARACTERISTICS ( $T_j=25$ unless otherwise specified)

$I_{GT}$	$V_D=12V R_L=33$	-	-	40	mA
$V_{GT}$		-	-	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=125 R_L=3.3K$	0.2	-	-	V
$I_L$	$I_G=1.2I_{GT}$	-	-	100	mA
$I_H$	$I_T=500mA$	-	-	90	mA
$dV/dt$	$V_D=1070V$ Gate Open $T_j=125$	1000	-	-	V/ $\mu$ s
$t_{on}$	$I_G=50mA I_A=500mA I_R=50mA$	-	7	-	$\mu$ s
$t_{off}$	$T_j=25$	-	100	-	

### STATIC CHARACTERISTICS

$V_{TM}$	$I_{TM}=50A t_p=380\mu s$	$T_j=25$	1.8	V
$V_{TO}$	Threshold voltage	$T_j=125$	0.74	V
$R_D$	Dynamic resistance	$T_j=125$	27	m
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	10	$\mu$ A
$I_{RRM}$		$T_j=125$	4	mA

### THERMAL RESISTANCES

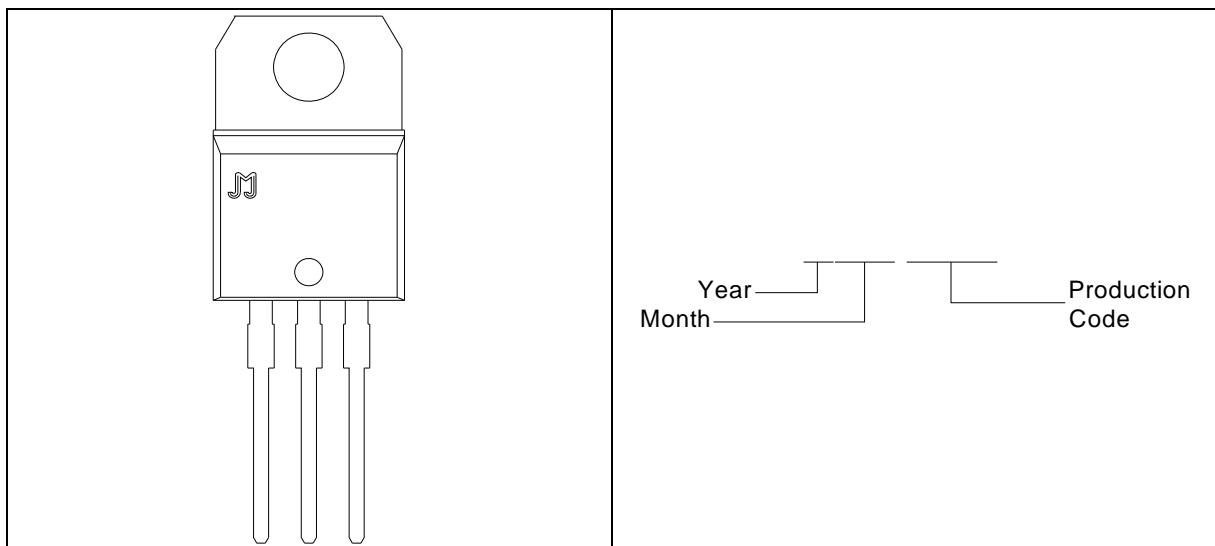
$R_{th(j-c)}$	junction to case(DC)	2.1	/W
$R_{th(j-a)}$	junction to ambient (DC)	65	/W



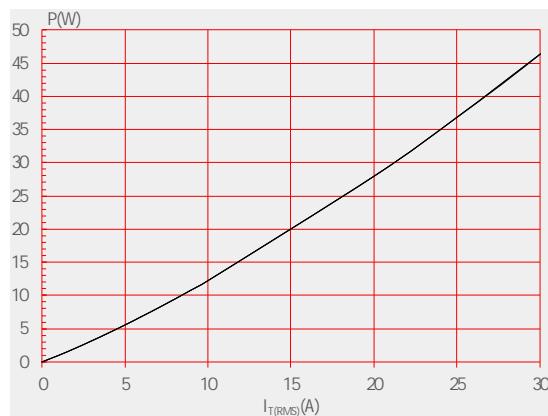
## ORDERING INFORMATION

J	CT	16	25	A
JieJie Microelectronics Co.,Ltd.	SCRs			
		16:V <sub>DRM</sub> /V <sub>RRM</sub> 1600V		I <sub>T(RMS)</sub> :25A
				A:TO-220A(Ins)

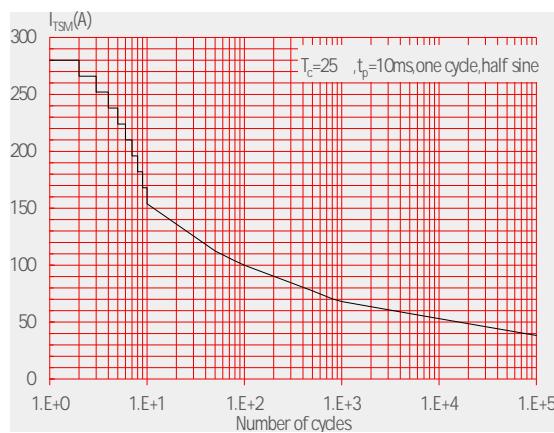
## MARKING



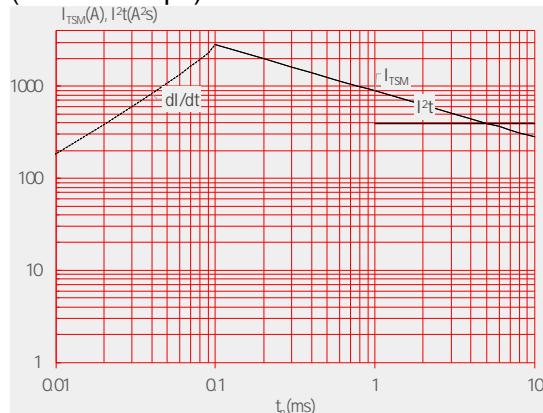
Maximum power dissipation versus RMS on-state current



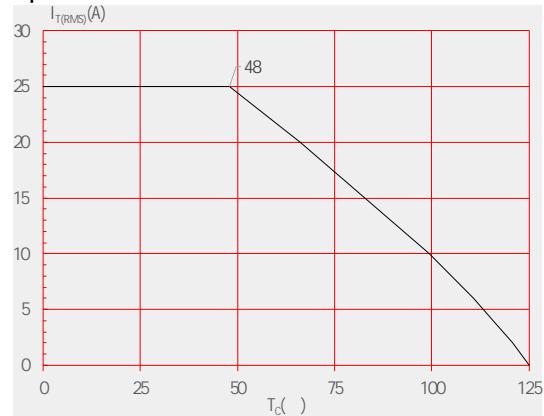
Surge peak on-state current versus number of cycles



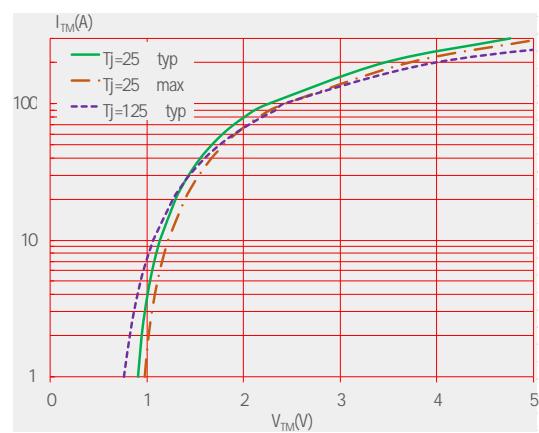
Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $\text{d}I/\text{dt} < 200\text{A}/\mu\text{s}$ )



RMS on-state current versus case temperature



On-state characteristics



Relative variations of gate trigger current, holding current and latching current versus junction temperature

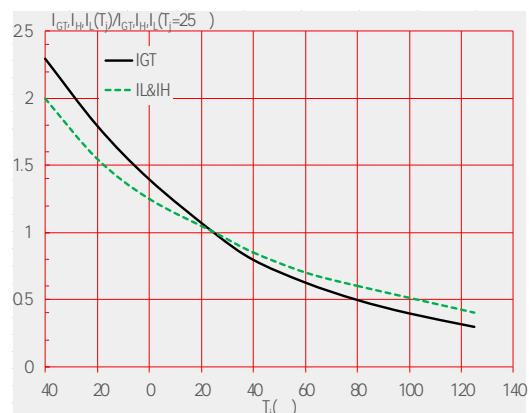
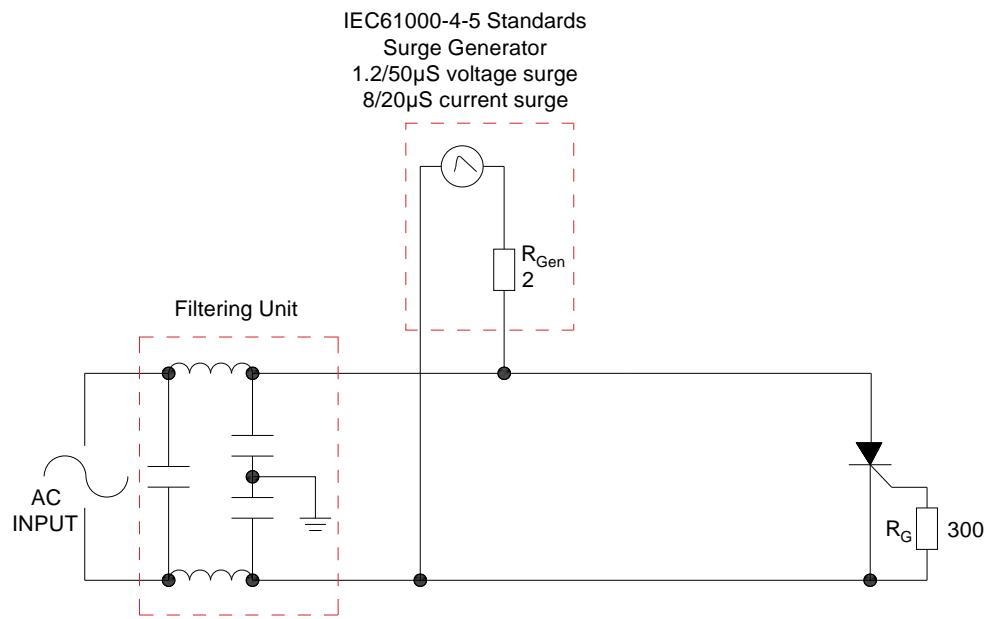




FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



## SHAPING AND SOLDERING PARAMETERS

Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie



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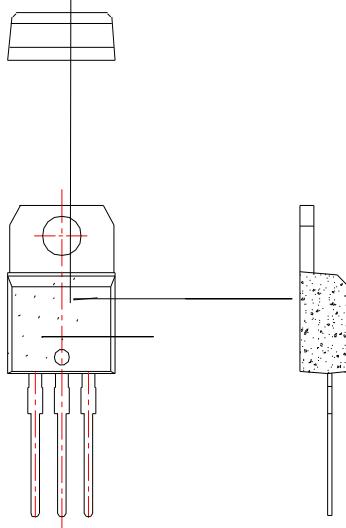
## ORDERING INFORMATION


Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update



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## PACKAGE MECHANICAL DATA





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